

PQMD10

NPN/PNP resistor-equipped transistors; R1 = 2.2 k Ω , R2 = 47 k Ω

4 November 2015

Product data sheet

1. General description

NPN/PNP double Resistor-Equipped Transistors (RET) in a leadless ultra small DFN1010B-6 (SOT1216) Surface-Mounted Device (SMD) plastic package.

NPN/NPN complement: PQMH10

2. Features and benefits

- 100 mA output current capability
- Built-in bias resistors
- Simplifies circuit design
- Low package height of 0.37 mm
- Reduces component count
- Reduces pick and place costs
- AEC-Q101 qualified

3. Applications

- Low current peripheral driver
- Control of IC inputs
- Replaces general-purpose transistors in digital applications
- Mobile applications

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit	
Per transistor	Per transistor; for the PNP transistor with negative polarity							
V_{CEO}	collector-emitter voltage	open base		-	-	50	V	
I _O	output current			-	-	100	mA	
Per transistor; for the PNP transistor with negative polarity								
R1	bias resistor 1	T _{amb} = 25 °C	[1]	1.54	2.2	2.86	kΩ	
R2/R1	bias resistor ratio		[1]	17	21	26		

^[1] See section "Test information" for resistor calculation and test conditions.



NPN/PNP resistor-equipped transistors; R1 = 2.2 k Ω , R2 = 47 k Ω

5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	GND1	GND (emitter) TR1	500	O1 I2 GND2
2	I1	input (base) TR1	$\begin{bmatrix} 1 \\ 7 \end{bmatrix} \begin{bmatrix} 6 \\ \end{bmatrix}$	
3	O2	output (collector) TR2	[2] [5]	R1 R2
4	GND2	GND (emitter) TR2		TR1 TR2
5	12	input (base) TR2	3 4	R2 R1
6	01	output (collector) TR1	Transparent top view	
7	01	output (collector) TR1	DFN1010B-6 (SOT1216)	GND1 I1 O2 aaa-007379
8	O2	output (collector) TR2		dad 557575

6. Ordering information

Table 3. Ordering information

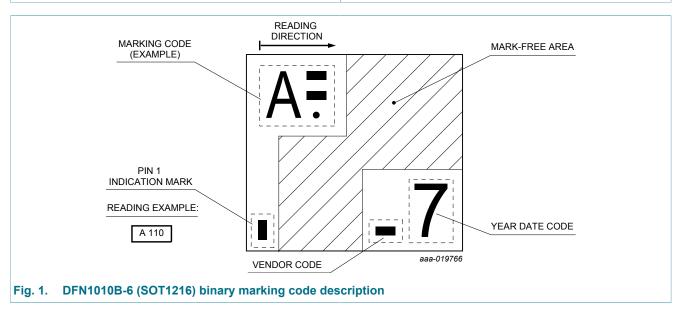
Type number	Package				
	Name	Description	Version		
PQMD10	DFN1010B-6	DFN1010B-6: plastic thermal enhanced ultra thin small outline package; no leads; 6 terminals	SOT1216		

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7. Marking

Table 4. Marking codes

Type number	Marking code
PQMD10	B 010



NPN/PNP resistor-equipped transistors; R1 = 2.2 k Ω , R2 = 47 k Ω

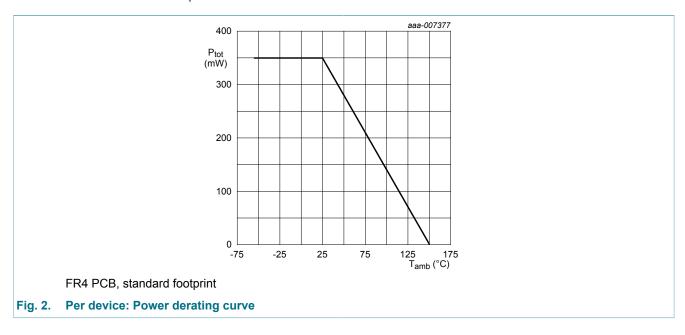
8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
Per transis	tor; for the PNP transistor with	negative polarity			'	,
V _{CBO}	collector-base voltage	open emitter		-	50	V
V _{CEO}	collector-emitter voltage	open base		-	50	V
V _{EBO}	emitter-base voltage	open collector		-	5	V
V _I input voltage	input voltage	TR1; positive		-	12	V
		TR1; negative		-	-5	V
		TR2; positive		-	5	V
		TR2; negative		-	-12	V
I _O	output current			-	100	mA
I _{CM}	peak collector current	t _p ≤ 1 ms; single pulse		-	100	mA
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C	[1]	-	230	mW
Per device						
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C	[1]	-	350	mW
Tj	junction temperature			-	150	°C
T _{amb}	ambient temperature			-55	150	°C
T _{stg}	storage temperature			-65	150	°C

[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.



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NPN/PNP resistor-equipped transistors; R1 = 2.2 k Ω , R2 = 47 k Ω

9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
Per transist	or						
$R_{\text{th(j-a)}}$	thermal resistance from junction to ambient	in free air	[1]	-	-	543	K/W
Per device							
$R_{\text{th(j-a)}}$	thermal resistance from junction to ambient	in free air	[1]	-	-	357	K/W

[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

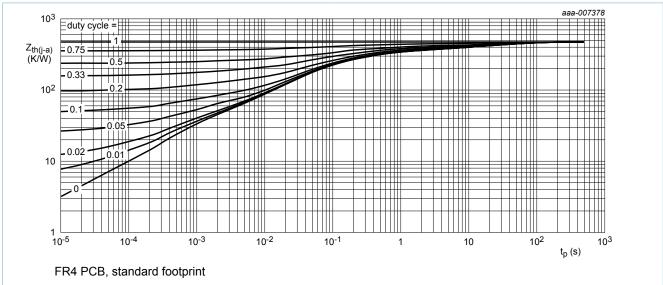


Fig. 3. Per transistor: Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

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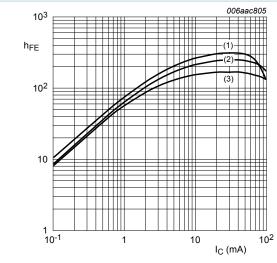
10. Characteristics

Table 7. **Characteristics**

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
Per transis	tor; for the PNP transistor	with negative polarity				'	_
I _{CBO}	collector-base cut-off current (emitter open)	$V_{CB} = 50 \text{ V}; I_{E} = 0 \text{ A}; T_{amb} = 25 \text{ °C}$		-	-	100	nA
OLO	collector-emitter cut-off	V _{CE} = 30 V; I _B = 0 A; T _{amb} = 25 °C		-	-	1	μA
	current (base open)	V _{CE} = 30 V; I _B = 0 A; T _{amb} = 150 °C		-	-	5	μA
I _{EBO}	emitter-base cut-off current (collector open)	$V_{EB} = 5 \text{ V}; I_{C} = 0 \text{ A}; T_{amb} = 25 \text{ °C}$		-	-	180	μA
h _{FE}	DC current gain	V_{CE} = 5 V; I_{C} = 10 mA; T_{amb} = 25 °C		100	-	-	
V _{CEsat}	collector-emitter saturation voltage	$I_C = 5 \text{ mA}; I_B = 0.25 \text{ mA}; T_{amb} = 25 ^{\circ}\text{C}$		-	-	100	mV
V _{I(off)}	off-state input voltage	$V_{CE} = 5 \text{ V}; I_{C} = 100 \mu\text{A}; T_{amb} = 25 ^{\circ}\text{C}$		-	0.6	0.5	V
V _{I(on)}	on-state input voltage	$V_{CE} = 0.3 \text{ V}; I_{C} = 5 \text{ mA}; T_{amb} = 25 ^{\circ}\text{C}$		1.1	0.75	-	V
R1	bias resistor 1	T _{amb} = 25 °C	[1]	1.54	2.2	2.86	kΩ
R2/R1	bias resistor ratio		[1]	17	21	26	
C _C	collector capacitance	$V_{CB} = 10 \text{ V}; I_E = 0 \text{ A}; f = 1 \text{ MHz};$ $T_{amb} = 25 \text{ °C}; TR1 \text{ (NPN)}$		-	-	2.5	pF
		V_{CB} = -10 V; I_{E} = 0 A; f = 1 MHz; T_{amb} = 25 °C; TR2 (PNP)		-	-	3	pF
f _T	transition frequency	V_{CE} = 5 V; I_{C} = 10 mA; f = 100 MHz; T_{amb} = 25 °C; TR1 (NPN)	[2]	-	230	-	MHz
		$V_{CE} = -5 \text{ V}; I_{C} = -10 \text{ mA}; f = 100 \text{ MHz};$ $T_{amb} = 25 \text{ °C}; TR2 \text{ (PNP)}$	[2]	-	180	-	MHz

See section "Test information" for resistor calculation and test conditions. Characteristics of built-in transistor

NPN/PNP resistor-equipped transistors; R1 = 2.2 k Ω , R2 = 47 k Ω



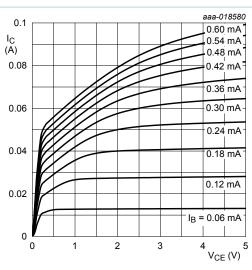
$$V_{CE} = 5 V$$

(1)
$$T_{amb} = 100 \, ^{\circ}C$$

(2)
$$T_{amb} = 25 \, ^{\circ}C$$

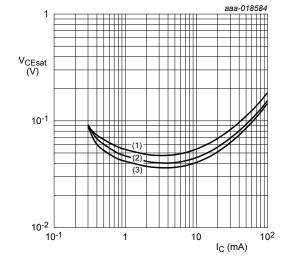
(3)
$$T_{amb} = -40 \, ^{\circ}C$$

Fig. 4. NPN transistor: DC current gain as a function of collector current; typical values



T_{amb} = 25 °C

Fig. 5. NPN transistor: Collector current as a function of collector-emitter voltage; typical values



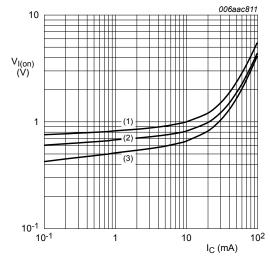
$$I_{\rm C}/I_{\rm B} = 20$$

(1)
$$T_{amb} = 100 \, ^{\circ}C$$

(2)
$$T_{amb}$$
 = 25 °C

(3)
$$T_{amb} = -40 \, ^{\circ}C$$

Fig. 6. NPN transistor: Collector-emitter saturation voltage as a function of collector current; typical values



$$V_{CE} = 0.3 V$$

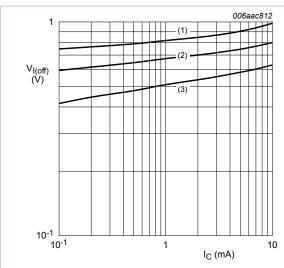
(1)
$$T_{amb} = -40 \, ^{\circ}C$$

(2)
$$T_{amb}$$
 = 25 °C

(3)
$$T_{amb} = 100 \, ^{\circ}C$$

Fig. 7. NPN transistor: On-state input voltage as a function of collector current; typical values

NPN/PNP resistor-equipped transistors; R1 = 2.2 k Ω , R2 = 47 k Ω



$$V_{CE} = 5 V$$

(1)
$$T_{amb} = -40 \, ^{\circ}C$$

(2)
$$T_{amb}$$
 = 25 °C

(3)
$$T_{amb}$$
 = 100 °C

Fig. 8. NPN transistor: Off-state input voltage as a function of collector current; typical values

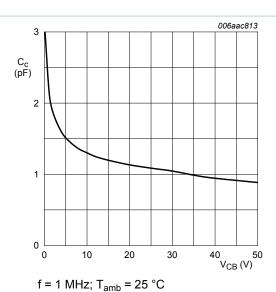


Fig. 9. NPN transistor: Collector capacitance as a function of collector-base voltage; typical values

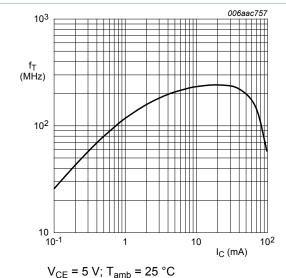
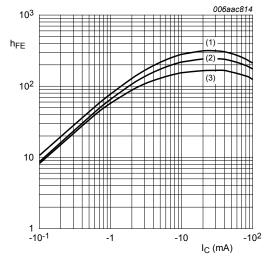


Fig. 10. NPN transistor: Transition frequency as a function of collector current; typical values of built-in transistor



$$V_{CE} = -5 V$$

(1)
$$T_{amb} = 100 \, ^{\circ}C$$

(2)
$$T_{amb}$$
 = 25 °C

(3)
$$T_{amb} = -40 \, ^{\circ}C$$

Fig. 11. PNP transistor: DC current gain as a function of collector current; typical values

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NPN/PNP resistor-equipped transistors; R1 = 2.2 k Ω , R2 = 47 k Ω

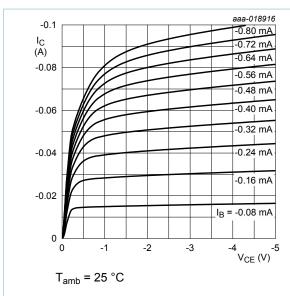
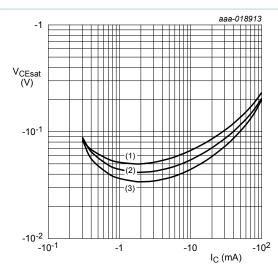


Fig. 12. PNP transistor: Collector current as a function of collector-emitter voltage; typical values



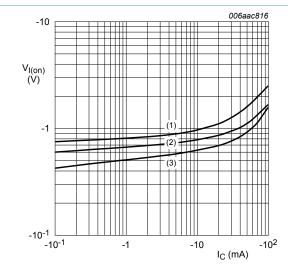
$$I_{\rm C}/I_{\rm B} = 20$$

(1)
$$T_{amb} = 100 \, ^{\circ}C$$

(2)
$$T_{amb} = 25 \, ^{\circ}C$$

(3)
$$T_{amb} = -40 \, ^{\circ}C$$

Fig. 13. PNP transistor: Collector-emitter saturation voltage as a function of collector current; typical values



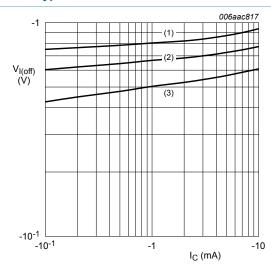
$$V_{CE}$$
 = -0.3 V

(1)
$$T_{amb} = -40 \, ^{\circ}C$$

(2)
$$T_{amb}$$
 = 25 °C

(3)
$$T_{amb}$$
 = 100 °C

Fig. 14. PNP transistor: On-state input voltage as a function of collector current; typical values



$$V_{CE} = -5 V$$

(1)
$$T_{amb} = -40 \, ^{\circ}C$$

(2)
$$T_{amb}$$
 = 25 °C

(3)
$$T_{amb}$$
 = 100 °C

Fig. 15. PNP transistor: Off-state input voltage as a function of collector current; typical values

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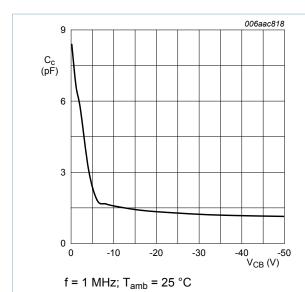


Fig. 16. PNP transistor: Collector capacitance as a function of collector-base voltage; typical values

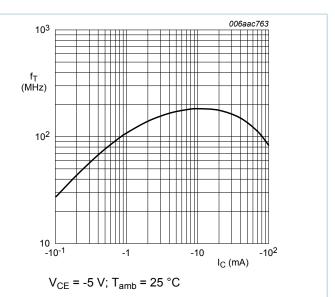


Fig. 17. PNP transistor: Transition frequency as a function of collector current; typical values of built-in transistor

11. Test information

11.1 Quality information

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard Q101 - Stress test qualification for discrete semiconductors, and is suitable for use in automotive applications.

11.2 Resistor calculation

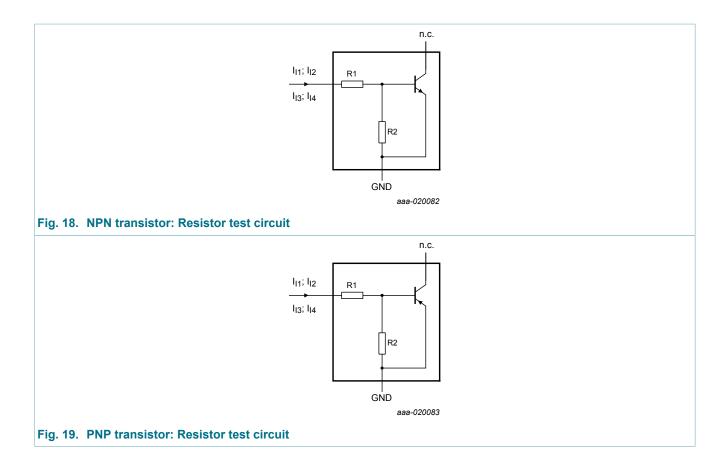
Calculation of bias resistor 1 (R1)

$$RI = \frac{V(I_{12}) - V(I_{11})}{I_{12} - I_{11}}$$

Calculation of bias resistor ratio (R2/R1)

$$\frac{R2}{R1} = \frac{V(I14) - V(I13)}{R1 \cdot (I14 - I13)} - 1$$

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11.3 Resistor test conditions

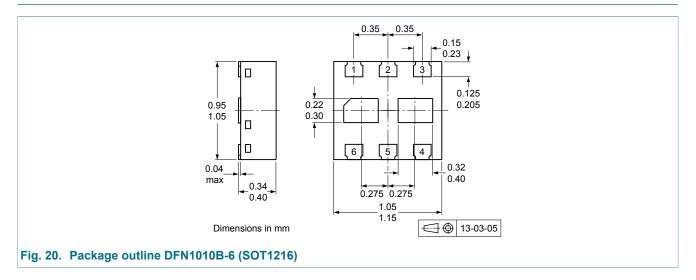
Table 8. Resistor test conditions

Per transistor; for the PNP transistor with negative polarity

R1 (kΩ)	R2 (kΩ) Test conditions				
		I _{II}	I ₁₂	I _{I3}	I ₁₄
2.2	47	90 μΑ	140 μΑ	-55 µA	-105 μA

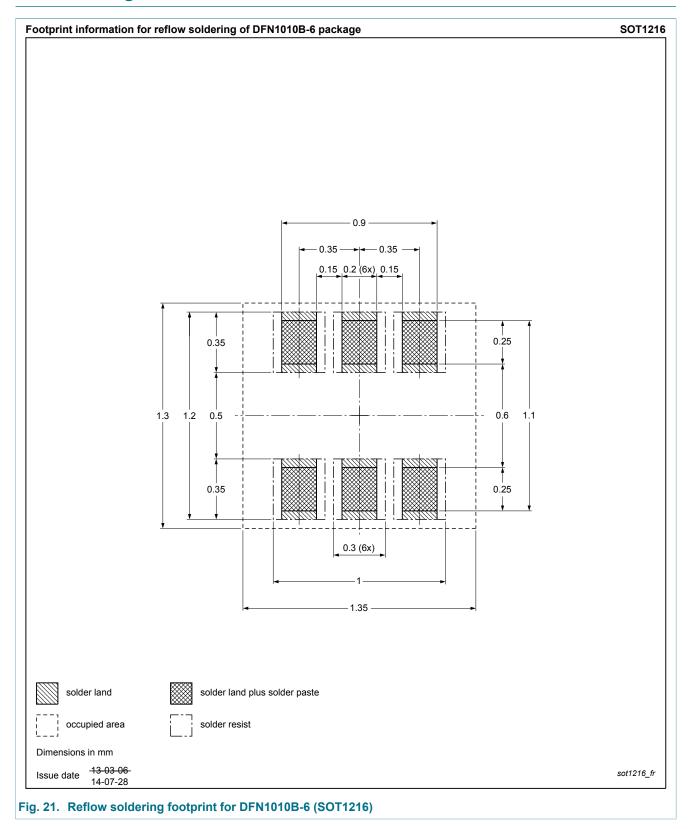
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12. Package outline



NPN/PNP resistor-equipped transistors; R1 = 2.2 k Ω , R2 = 47 k Ω

13. Soldering



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NPN/PNP resistor-equipped transistors; R1 = 2.2 k Ω , R2 = 47 k Ω

14. Revision history

Table 9. Revision history

Data sheet ID	Release date	Data sheet status	Change notice	Supersedes
PQMD10 v.1	20151104	Product data sheet	-	-

NPN/PNP resistor-equipped transistors; R1 = 2.2 k Ω , R2 = 47 k Ω

15. Legal information

15.1 Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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